NSN 5961-01-128-3316

Unitized Semiconductor Devices - Page 1 of 1

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Inclosure Material:

Plastic

Overall Length:

Between 0.300 inches and 0.330 inches

Overall Height:

Between 0.030 inches and 0.080 inches

Overall Width:

Between 0.240 inches and 0.290 inches

Component Name And Quantity:

4 transistor

Mounting Method:

Press fit

Features Provided:

Burn in and hermetically sealed case

Semiconductor Material:

Silicon all transistor

Voltage Rating In Volts Per Characteristic:

40.0 collector to base voltage/static/emitter open all transistor and 40.0 collector to emitter voltage/static/base open all transistor and 5.0 emitter to base voltage, static, collector open all transistor

Current Rating Per Characteristic:

1.50 amperes source cutoff current all transistor

Power Rating Per Characteristic:

4.0 watts small-signal input power, common-collector preset all transistor

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

Special Features:

All transistor junction pattern arrangement: pnp

Terminal Type And Quantity:

14 ribbon

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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